PROTECTION OF REACTIVE METAL SURFACES OF SEMICONDUCTOR DEVICES DURING SHIPPING BY PROVIDING AN ADDITIONAL PROTECTION LAYER

ABSTRACT

When forming complex metallization systems on the basis of copper, the very last metallization layer may receive contact regions on the basis of copper, the surface of which may be passivated on the basis of a dedicated protection layer, which may thus allow the patterning of the passivation layer stack prior to shipping the device to a remote manufacturing site. Hence, the protected contact surface may efficiently be re-exposed in the remote manufacturing site on the basis of an efficient non-masked wet chemical etch process.

Figure 2d